

FEATURES OF DOPING OF THE  $p$ -TiCoSb  
INTERMETALLIC SEMICONDUCTOR WITH  
A Cu DONOR IMPURITY. 1. CALCULATION  
OF ELECTRON STRUCTURE

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S u m m a r y

The band structure and the density of states (DOS) in an intermetallic semiconductor TiCoSb doped with a donor impurity by substituting Co atoms by Cu ones have been calculated. The dependence of the Fermi level position on the donor impurity concentration has been found. Possible mechanisms of conductivity at various concentrations of the donor impurity have been analyzed.